IN THE SPECIFICATION:

Please replace paragraph number **[0001]** with the following rewritten paragraph:

[0001] This application is a continuation of application Serial No. 09/651,460, filed August 30, 2000, now U.S. Patent ~~6,295,209 B1,~~ 6,295,209, issued September 25, 2001, which is a continuation of application Serial No. 09/464,992, filed December 16, 1999, now U.S. Patent 6,144,560, issued November 7, 2000, which is a continuation of application Serial No. 09/296,952, filed April 22, 1999, now U.S. Patent 6,091,606, issued July 18, 2000, which is a continuation of application Serial No. 09/002,063, filed December 31, 1997, now U.S. Patent 5,940,277, issued August 17, 1999.

Please replace paragraph number **[0008]** with the following rewritten paragraph:

[0008] United States Patent 5,593,927 (the ~~"927 patent),~~ "'927 patent"), issued to Warren M. Farnworth et al. on January 14, 1997, discloses a method of minimally packaging semiconductor devices which includes forming a protective layer of glass, silicon nitride, silicon dioxide, or polyimide and additional conductive traces on the surface thereof. The thickness of such protective layers is in the range of only about 1 μm to 12.5 μm (½ mil), making them somewhat undesirable. When disposed on vertically mountable semiconductor devices, such protective layers would lend little or no support to the device. Similarly, when placed in a holder such as the one that is disclosed in the '927 patent, the protective layer is too thin to align electrical connectors of the holder with their corresponding bond pads on the semiconductor device.

Please replace paragraph number **[0030]** with the following rewritten paragraph:

[0030] With reference to FIG. 4, another variation of the overcoat layer 16″ is shown. Overcoat layer 16″ has a substantially uniform thickness, imparting semiconductor device 10″ with a squared ~~bottom~~ edge 15″. Thus, teeth 19a″, 19b″, 19c″, etc. include squared ends. Other variations of the overcoat layer may form teeth which include rounded ends between each of the bond pads or may define notches which totally surround the bond pads.

Please replace paragraph number **[0031]** with the following rewritten paragraph:

[0031] Overcoat layer 16 is preferably manufactured from a durable material which can be applied to a semiconductor device in a relatively thick layer (at least about one mil (25μm) thick) and which may be formed into desired shapes of very fine resolution (i.e., about 1μm and lower). Some photoimageable epoxies are useful as overcoat layer 16. One such material is the multi-functional glycidyl ether derivative of bisphenol-A novolac high-resolution negative ~~photoresist~~ photoresist, available from Shell Chemical Company of Houston, ~~Texas~~ Texas, under the trade name EPON® SU-8. EPON® SU-8 is a low molecular weight resin which is useful for fabricating structures having dimensions in the lower range of about 0.25μm to about 0.10μm. As employed in the present invention, however, the multi-functional glycidyl ether derivative of bisphenol-A novolac is useful for forming overcoat layers of up to about 250μm (10 mils) thick. When combined with a ~~photoinitiator,~~ photoinitiator or promoter, the photoimageable epoxy forms a highly structured, cross-linked matrix. One such photoinitiator is triaryl sulfonium salt, which is available from Union Carbide Corporation of Danbury, Connecticut under the trade name CYRACURE® UVI. That highly structured, cross-linked matrix may then be solvated in organic solvents such as gamma-butyrolactone, propylene glycol methyl ether acetate, and methyl isobutyl ketone. Other photoinitiators are also useful for forming such cross-linked matrices with multi-functional glycidyl ether derivatives of bisphenol-A novolac such as EPON® SU-8.